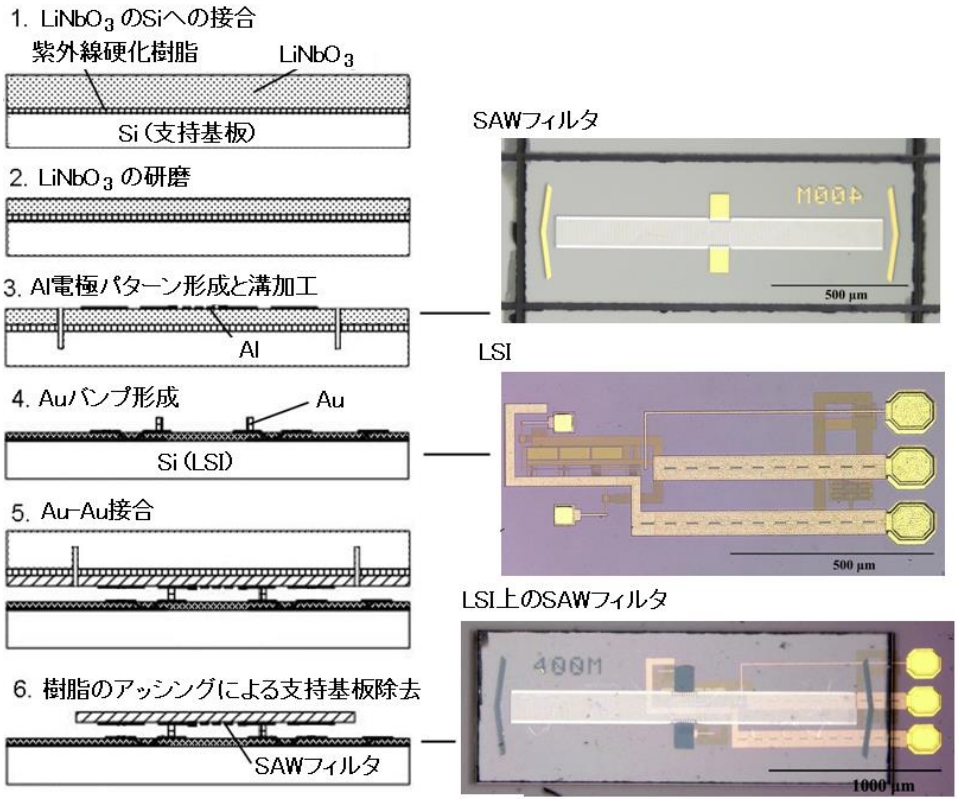
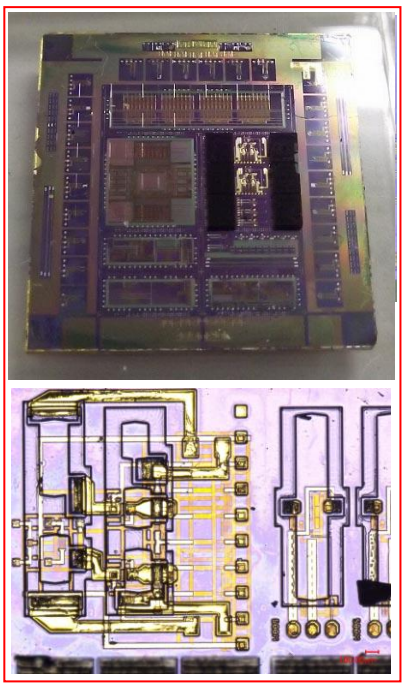
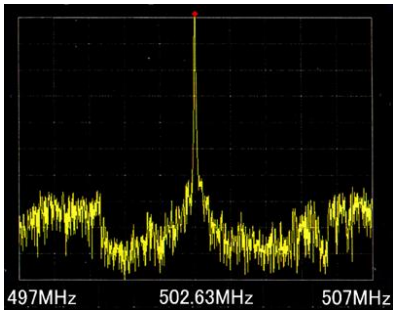
A12

# SAW デバイス on LSI（集積回路上の表面弾性波素子）

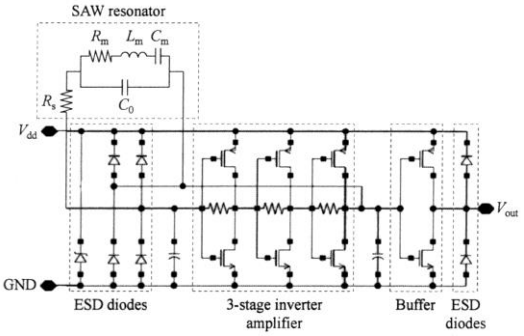



製作工程

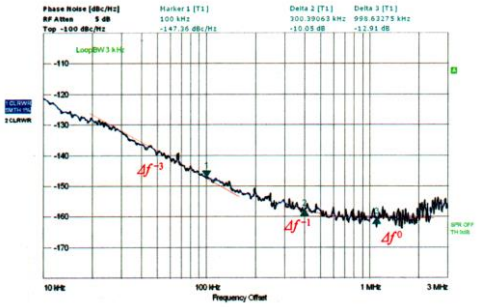





発振スペクトル

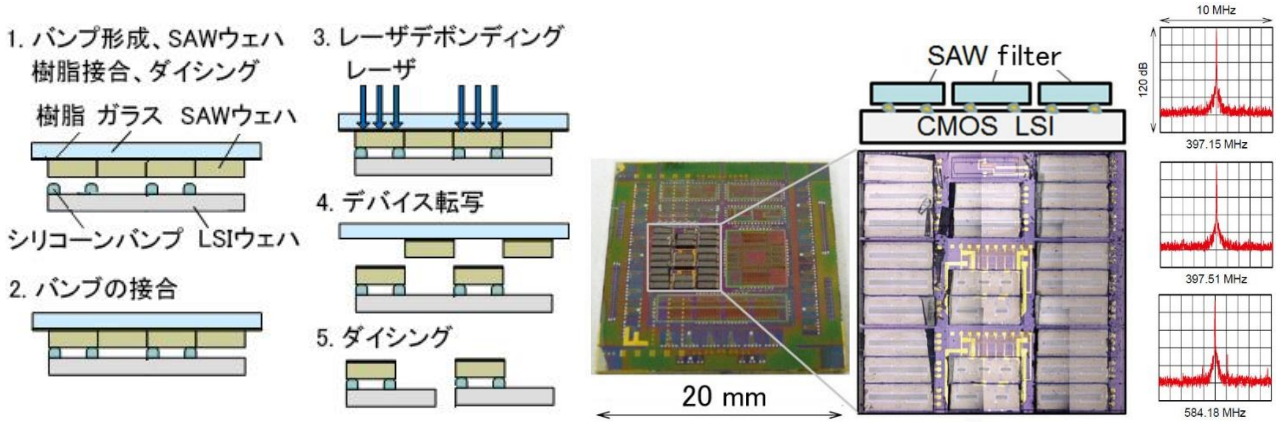



集積回路




ジッター特性

参考文献 ：K.D.Park, M.Esashi and S.Tanaka, Preparation of Thin Lithium Niobate Layer on Silicon Wafer for Wafer-level Integration of Acoustic Devices and LSI, 電気学会論文誌E, 130-E (2010) pp.236-241




選択転写工程とそれを用いた LSI 上マルチ SAW フィルタ

Reference ; S. Tanaka, M. Yoshida, H. Hirano and M. Esashi, Lithium Niobate SAW Device Hetero-transferred onto Silicon Integrated Circuit Using Elastic and Sticky Bumps, 2012 IEEE International Ultrasonics Sympsium (2012) p.1047